HARRIS SEMICONDUCTOR

CD54HC00, CD54HCT00, CD74HC00, CD74HC00

High Speed CMOS Logic Quad 2-Input NAND Gate

May 1997

Features

- Buffered Inputs
- Typical Propagation Delay: 7ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}
- Related Literature
  - CD54HC00F3A and CD54HCT00F3A Military Data Sheet, Document Number 3753

Description

The Harris CD54HC00, CD54HCT00, CD74HC00 and CD74HCT00 logic gates utilize silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 74HCT logic family is functionally pin compatible with the standard 74LS logic family.

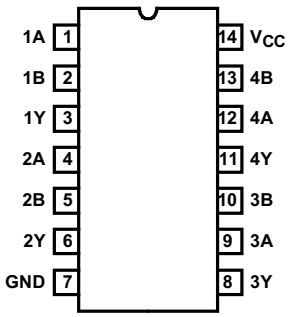
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC00E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT00E	-55 to 125	14 Ld PDIP	E14.3
CD74HC00M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT00M	-55 to 125	14 Ld SOIC	M14.15
CD54HC00F	-55 to 125	14 Ld CERDIP	F14.3
CD54HCT00F	-55 to 125	14 Ld CERDIP	F14.3
CD54HC00W	-55 to 125	Wafer	
CD54HCT00W	-55 to 125	Wafer	
CD54HC00H	-55 to 125	Die	
CD54HCT00H	-55 to 125	Die	

NOTE: When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

Pinout

CD54HC00, CD54HCT00, CD74HC00, CD74HCT00
(PDIP, CERDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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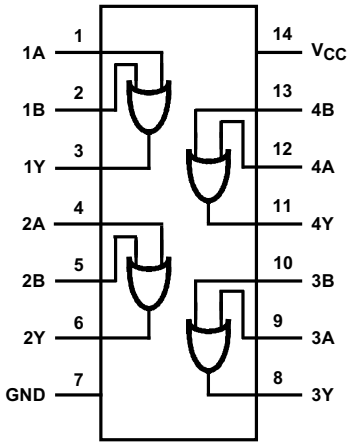
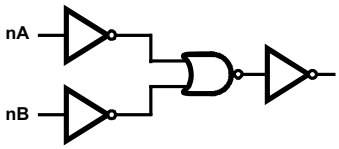
Functional Diagram



TRUTH TABLE

INPUTS		OUTPUT
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

Logic Symbol



Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
PDIP Package	100	N/A
CERDIP Package		
SOIC Package	180	N/A

Maximum Junction Temperature (Hermetic Package or Die) . . . 175°C
Maximum Junction Temperature (Plastic Package) . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	2	-	20	-	40	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-0.02	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	-4	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			0.02	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	4	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	2	-	20	-	40	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC}	V_{CC} - 2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

2. For dual-supply systems theorectical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nA	1.8
nB	1.1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g. 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, Input to Output (Figure 1)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	90	-	115	-	135	ns
			4.5	-	-	18	-	23	-	27	ns
			6	-	-	15	-	20	-	23	ns
Propagation Delay, Data Input to Output Y	t_{PLH}, t_{PHL}	C_L = 15pF	5	-	7	-	-	-	-	-	pF

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	18	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	25	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay, Input to Output (Figure 2)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	20	-	25	-	30	ns
Propagation Delay, Data Input to Output Y	t_{PLH}, t_{PHL}	C_L = 15pF	5	-	8	-	-	-	-	-	pF
Transition Times (Figure 2)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	25	-	-	-	-	-	pF

NOTES:

3. C_{PD} is used to determine the dynamic power consumption, per gate.
4. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms

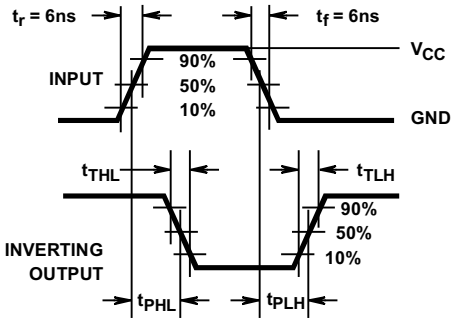


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

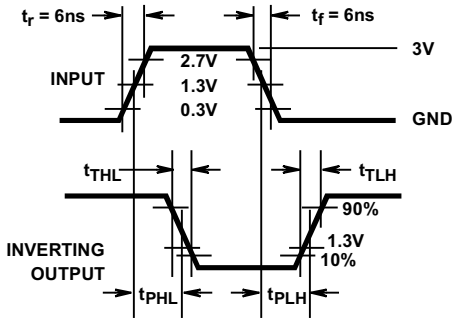


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

INPUT LEVEL	HC TYPES	HCT TYPES
	V_{CC}	3V
V_S	50% V_{CC}	1.3V

NOTE: Transition times and propagation delay times.